

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK1530

High Power Amplifier Application

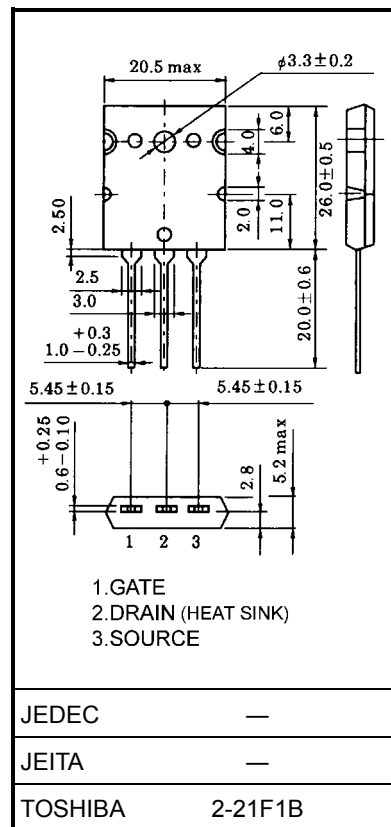
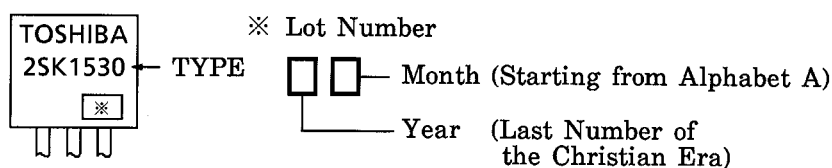
Unit: mm

- High breakdown voltage : $V_{DSS} = 200V$
- High forward transfer admittance : $|Y_{fs}| = 5.0 S (typ.)$
- Complementary to 2SJ201

Maximum Ratings ($T_a = 25^\circ C$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	200	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current (Note 1)	I_D	12	A
Drain power dissipation ($T_c = 25^\circ C$)	P_D	150	W
Channel temperature	T_c	150	$^\circ C$
Storage temperature range	T_{stg}	$-55 \sim 150$	$^\circ C$

Marking



Weight: 9.75 g (typ.)

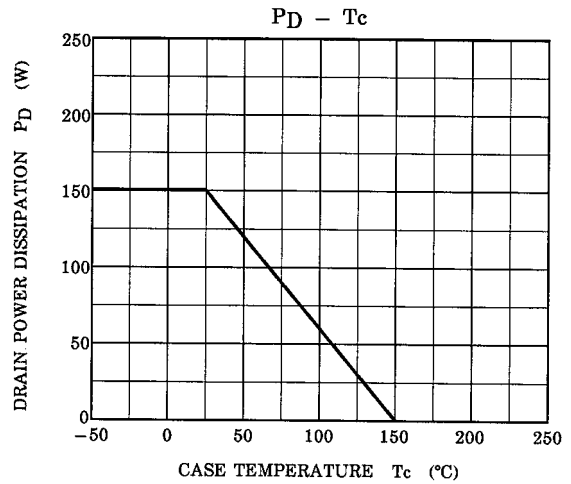
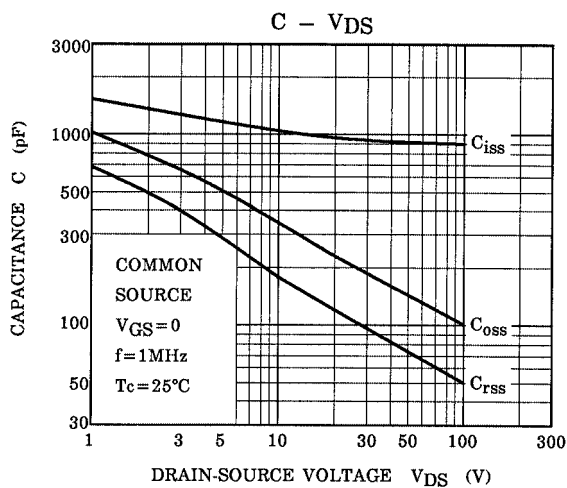
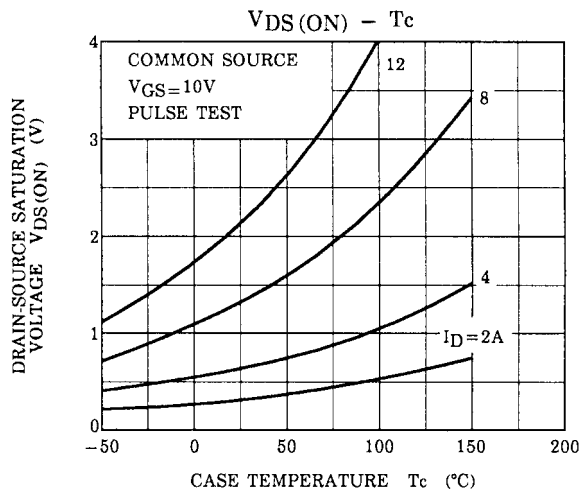
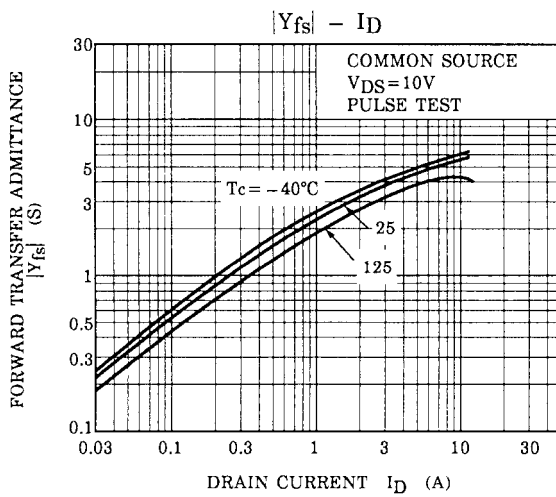
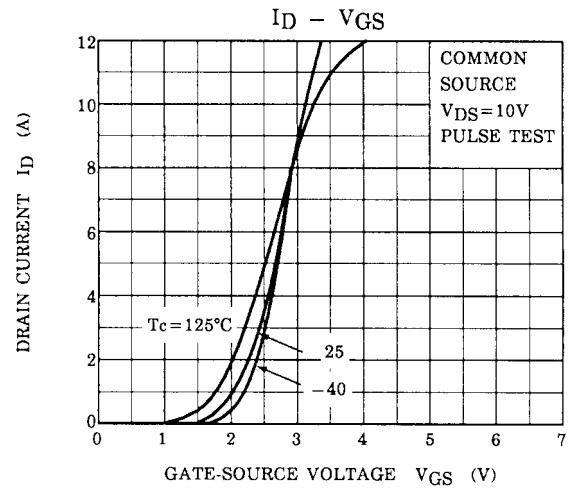
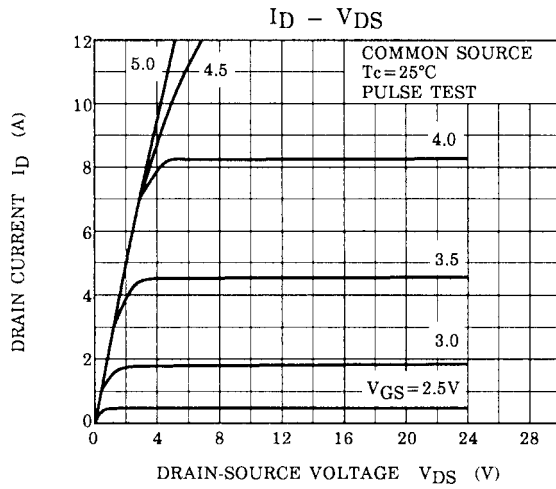
Electrical Characteristics ($T_a = 25^\circ C$)

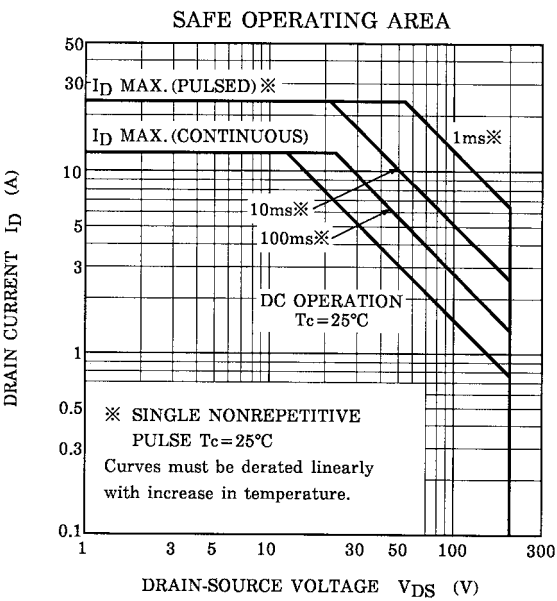
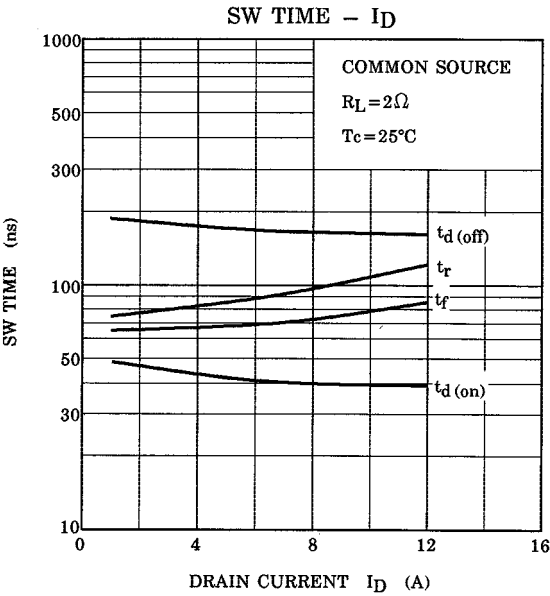
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain cut-off current	I_{DSS}	$V_{DS} = 200 V, V_{GS} = 0$	—	—	1.0	mA
Gate leakage current	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	—	—	± 0.5	μA
Drain-source breakdown voltage	$V_{(BR) DSS}$	$I_D = 10 mA, V_{GS} = 0$	200	—	—	V
Drain-source saturation voltage	$V_{DS (ON)}$	$I_D = 8 A, V_{GS} = 10 V$	—	2.5	5.0	V
Gate-source cut-off voltage (Note 2)	$V_{GS (OFF)}$	$V_{DS} = 10 V, I_D = 0.1 A$	0.8	—	2.8	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10 V, I_D = 5 A$	—	5.0	—	S
Input capacitance	C_{iss}	$V_{DS} = 30 V, V_{GS} = 0, f = 1 MHz$	—	900	—	pF
Output capacitance	C_{oss}	$V_{DS} = 30 V, V_{GS} = 0, f = 1 MHz$	—	180	—	
Reverse transfer capacitance	C_{rss}	$V_{DD} = 30 V, V_{GS} = 0, f = 1 MHz$	—	100	—	

Note 1: Please use devices on condition that the channel temperature is below $150^\circ C$.

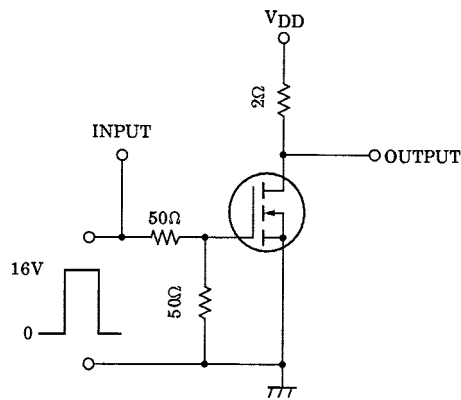
Note 2: $V_{GS (OFF)}$ Classification 0: 0.8~1.6 Y: 1.4~2.8

This transistor is an electrostatic sensitive device.
Please handle with caution.

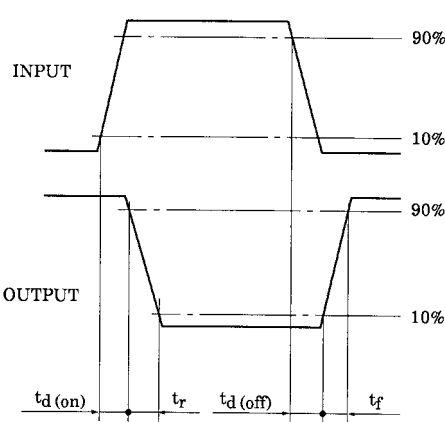




Switching Time Test Circuit



Waveforms



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